

EH3500TTS-18.432M TR



ITEM DESCRIPTION

Quartz Crystal Clock Oscillators XO (SPXO) HCMOS/TTL (CMOS) 5.0Vdc 4 Pad 3.2mm x 5.0mm Ceramic Surface Mount (SMD) 18.432MHz ± 100 ppm 0°C to +70°C

ELECTRICAL SPECIFICATIONS

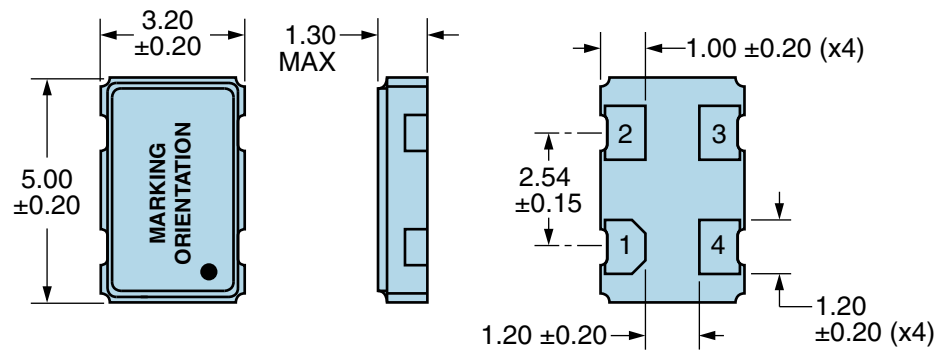
Nominal Frequency	18.432MHz
Frequency Tolerance/Stability	± 100 ppm Maximum (Inclusive of all conditions: Calibration Tolerance at 25°C, Frequency Stability over the Operating Temperature Range, Supply Voltage Change, Output Load Change, 1st Year Aging at 25°C, Shock, and Vibration)
Aging at 25°C	± 5 ppm/year Maximum
Operating Temperature Range	0°C to +70°C
Supply Voltage	5.0Vdc $\pm 10\%$
Input Current	50mA Maximum (No Load)
Output Voltage Logic High (Voh)	2.4Vdc Minimum with TTL Load, Vdd-0.4Vdc Minimum with HCMOS Load (IOH = -16mA)
Output Voltage Logic Low (Vol)	0.4Vdc Maximum with TTL Load, 0.5Vdc Maximum with HCMOS Load (IOL = +16mA)
Rise/Fall Time	6nSec Maximum (Measured at 0.8Vdc to 2.0Vdc with TTL Load or at 20% to 80% of waveform with HCMOS Load)
Duty Cycle	50 ± 5 (%) (Measured at 50% of waveform with TTL Load or with HCMOS Load)
Load Drive Capability	10TTL Load or 50pF HCMOS Load Maximum
Output Logic Type	CMOS
Pin 1 Connection	Tri-State (Disabled Output: High Impedance)
Tri-State Input Voltage (Vih and Vil)	+2.2Vdc Minimum to enable output, +0.8Vdc Maximum to disable output (High Impedance), No Connect to enable output.
Absolute Clock Jitter	± 250 pSec Maximum, ± 100 pSec Typical
One Sigma Clock Period Jitter	± 50 pSec Maximum, ± 30 pSec Typical
Start Up Time	10mSec Maximum
Storage Temperature Range	-55°C to +125°C

ENVIRONMENTAL & MECHANICAL SPECIFICATIONS

Fine Leak Test	MIL-STD-883, Method 1014, Condition A
Gross Leak Test	MIL-STD-883, Method 1014, Condition C
Mechanical Shock	MIL-STD-202, Method 213, Condition C
Resistance to Soldering Heat	MIL-STD-202, Method 210
Resistance to Solvents	MIL-STD-202, Method 215
Solderability	MIL-STD-883, Method 2003
Temperature Cycling	MIL-STD-883, Method 1010
Vibration	MIL-STD-883, Method 2007, Condition A

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MECHANICAL DIMENSIONS (all dimensions in millimeters)

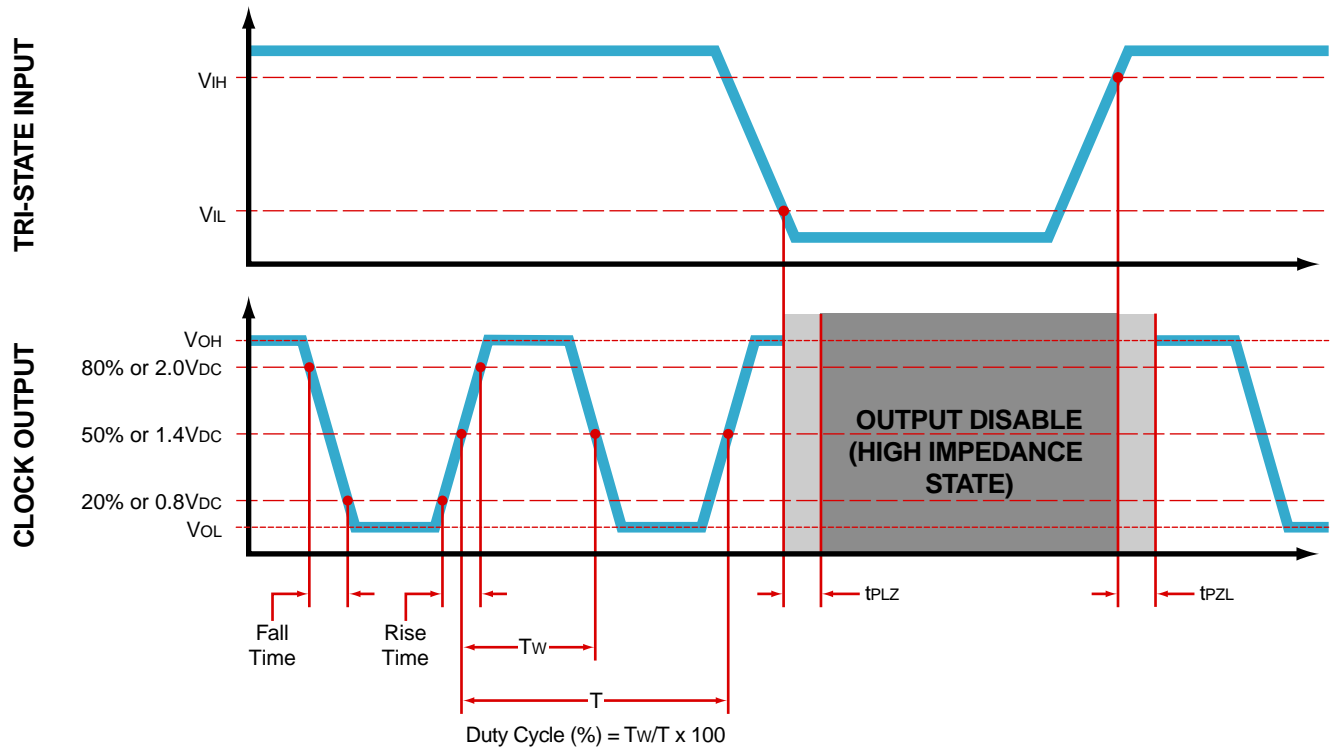


PIN	CONNECTION
1	Tri-State
2	Ground/Case Ground
3	Output
4	Supply Voltage

LINE	MARKING
1	E18.432 <i>E=Ecliptek Designator</i>
2	XXXXX <i>XXXXX=Ecliptek Manufacturing Identifier</i>

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OUTPUT WAVEFORM & TIMING DIAGRAM

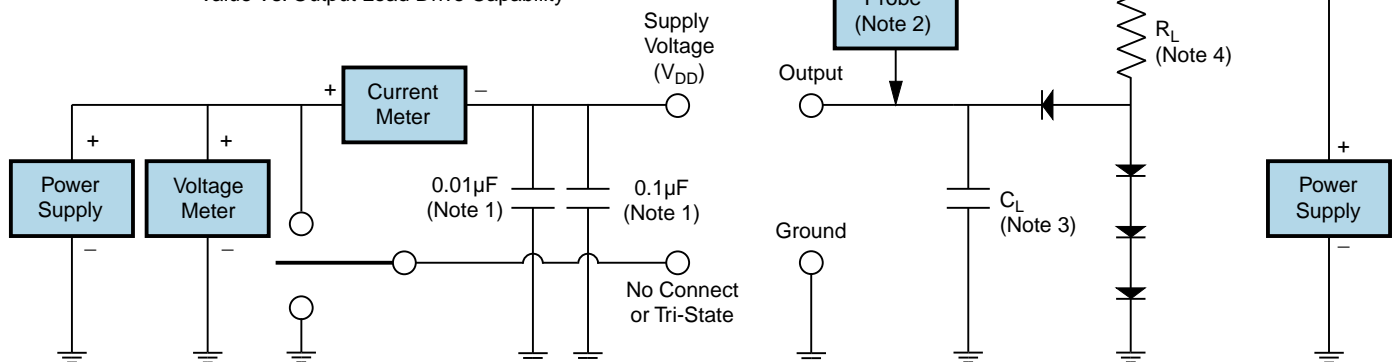


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Test Circuit for TTL Output

Output Load Drive Capability	R_L Value (Ohms)	C_L Value (pF)
10TTL	390	15
5TTL	780	15
2TTL	1100	6
10LSTTL	2000	15
1TTL	2200	3

Table 1: R_L Resistance Value and C_L Capacitance Value Vs. Output Load Drive Capability



Note 1: An external $0.1\mu\text{F}$ low frequency tantalum bypass capacitor in parallel with a $0.01\mu\text{F}$ high frequency ceramic bypass capacitor close to the package ground and V_{DD} pin is required.

Note 2: A low capacitance ($<12\text{pF}$), 10X attenuation factor, high impedance ($>10\text{Mohms}$), and high bandwidth ($>300\text{MHz}$) passive probe is recommended.

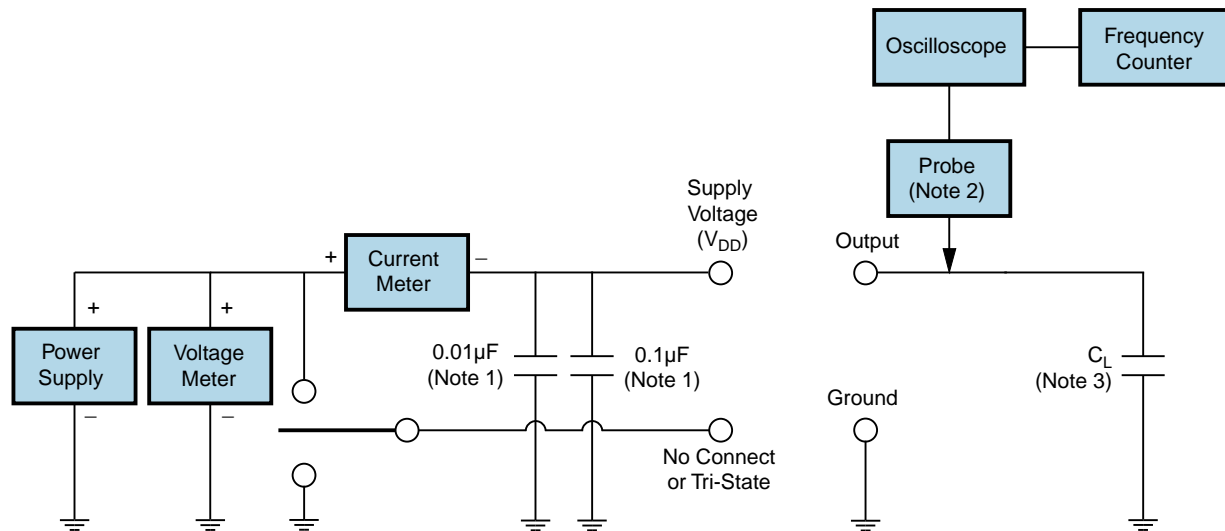
Note 3: Capacitance value C_L includes sum of all probe and fixture capacitance.

Note 4: Resistance value R_L is shown in Table 1. See applicable specification sheet for 'Load Drive Capability'.

Note 5: All diodes are MMBD7000, MMBD914, or equivalent.

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Test Circuit for CMOS Output



Note 1: An external $0.1\mu\text{F}$ low frequency tantalum bypass capacitor in parallel with a $0.01\mu\text{F}$ high frequency ceramic bypass capacitor close to the package ground and V_{DD} pin is required.

Note 2: A low capacitance ($<12\text{pF}$), 10X attenuation factor, high impedance ($>10\text{Mohms}$), and high bandwidth ($>300\text{MHz}$) passive probe is recommended.

Note 3: Capacitance value C_L includes sum of all probe and fixture capacitance.